

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

215686US99CIP

SERIAL NO.

09/985,757

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Fred RICHARD, et al.

FILING DATE

November 6, 2001

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA	3,802,967	04/09/74	Ladany et al.			
AB	4,174,422	11/13/79	Mathews et al.			
AC	4,404,265	09/13/83	Manasevit			
AD	4,482,906	11/13/84	Hovel et al.			
AE	4,523,211	06/11/85	Morimoto et al.			
AF	4,661,176	04/28/87	Manasevit			
AG	4,793,872	12/27/88	Meunier et al.			
AH	4,846,926	07/11/89	Kay et al.			
AJ	4,855,249	08/08/89	Akasaki et al.			
AI	4,891,091	01/02/90	Shastri			
AK	4,912,087	03/27/90	Aslam et al.			
AL	4,928,154	05/22/90	Umeno et al.			
AM	4,963,949	10/16/90	Wanlass et al.			
AN	5,141,894	08/25/92	Bisaro et al.			
AO	5,159,413	10/27/92	Calviello et al.			
AP	5,173,474	12/22/92	Connell et al.			
AQ	5,221,367	06/22/93	Chisholm et al.			
AR	5,225,031	07/06/93	McKee et al.			
AS	5,358,925	10/25/94	Neville Connell et al.			
AT	5,393,352	02/28/95	Summerfelt			
AU	5,418,216	05/23/95	Fork			
AV	5,450,812	09/19/95	McKee et al.			
AW	5,478,653	12/26/95	Guenzer			
AX	5,482,003	01/09/96	McKee et al.			
AY	5,514,484	05/07/96	Nashimoto			
AZ	5,556,463	09/17/96	Guenzer			
BA	5,588,995	12/31/96	Sheldon			
BB	5,670,798	09/23/97	Schetzina			
BC	5,733,641	03/31/98	Fork et al.			
BD	5,735,949	04/07/98	Manti et al.			
BE	5,741,724	04/21/98	Ramdani et al.			
BF	5,810,923	09/22/98	Yano et al.			
BG	5,830,270	11/03/98	McKee et al.			
BH	5,912,068	06/15/99	Jia			
BI	6,020,222	02/01/00	Wollesen			
BJ	6,045,626	04/04/00	Yano et al.			
BK	6,064,078	05/16/00	Northrup et al.			
BL	6,064,092	05/16/00	Park			
BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
BN	6,103,008	08/15/00	McKee et al.			
BO	6,136,666	10/24/00	So			
BP	6,174,755	01/16/01	Manning			



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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CA		3,766,370	10/16/73	Walther			
CB		4,006,989	02/08/77	Andringa			
CC		4,284,329	08/18/81	Smith et al.			
CD		4,777,613	10/11/98	Shahan et al.			
CE		4,802,182	01/31/89	Thomton et al.			
CF		4,882,300	11/21/89	Inoue et al.			
CG		4,896,194	01/23/90	Suzuki			
CH		4,999,842	03/12/91	Huang et al.			
CI		5,081,062	01/14/92	Vasudev et al.			
CJ		5,155,658	10/13/92	Inam et al.			
CK		5,248,564	09/28/93	Ramesh			
CL		5,260,394	11/09/93	Tazaki et al.			
CM		5,270,298	12/14/93	Ramesh			
CN		5,286,985	02/15/94	Taddiken			
CO		5,310,707	05/10/94	Oishi et al.			
CP		5,326,721	07/05/94	Summerfelt			
CQ		5,404,581	04/04/95	Honjo			
CR		5,418,389	05/23/95	Watanabe			
CS		5,436,759	07/25/95	Dijali et al.			
CT		5,576,879	11/19/96	Nashimoto			
CU		5,606,184	02/25/97	Abrokwah, et al.			
CV		5,640,267	06/17/97	May et al.			
CW		5,674,366	10/07/97	Hayashi et al.			
CX		5,729,641	03/17/98	Chandonnet et al.			
CY		5,790,583	08/04/98	Ho			
CZ		5,825,799	10/20/98	Ho et al.			
DA		5,857,049	01/05/99	Beranek et al.			
DB		5,874,860	02/23/99	Brunel et al.			
DC		5,926,496	07/20/99	Ho et al.			
DD		5,937,285	08/10/99	Abrokwah, et al.			
DE		5,981,400	11/09/99	Lo			
DF		5,990,495	11/23/99	Ohba			
DG		6,002,375	12/14/99	Corman et al.			
DH		6,008,762	12/28/99	Nghiem			
DI		6,055,179	04/25/00	Koganei et al.			
DJ		6,107,653	08/22/00	Fitzgerald			
DK		6,113,690	09/05/00	Yu et al.			
DL		6,114,996	09/05/00	Nghiem			
DM		6,121,642	09/19/00	Newns			
DN		6,128,178	10/03/00	Newns			
DO		6,143,072	11/07/00	McKee et al.			

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EA		4,484,332	11/20/84	Hawrylo			
EB		4,815,084	03/21/89	Scifres et al.			
EC		4,876,219	10/24/89	Eshita et al.			
ED		4,963,508	10/16/90	Umeno et al.			
EE		5,060,031	10/22/91	Abrokwah, et al.			
EF		5,063,166	11/05/91	Mooney et al.			
EG		5,116,461	05/26/92	Lebby et al.			
EH		5,127,067	06/30/92	Delcoco et al.			
EI		5,144,400	09/01/92	Ma			
EJ		5,293,050	03/08/94	Chapple-Sokol et al			
EK		5,356,831	10/18/94	Calviello et al.			
EL		5,391,515	02/21/95	Kao et al.			
EM		5,442,191	08/15/95	Ma			
EN		5,444,016	08/22/95	Abrokwah, et al.			
EO		5,480,829	01/02/96	Abrokwah, et al.			
EP		5,528,414	06/18/96	Oakley			
EQ		5,614,739	03/25/97	Abrokwah et al.			
ER		5,729,394	03/17/98	Sevier et al.			
ES		5,731,220	03/24/98	Tsu et al.			
ET		5,764,676	06/09/98	Paoli et al.			
EU		5,777,762	07/07/98	Yamamoto			
EV		5,778,018	07/07/98	Yoshikawa et al.			
EW		5,778,116	07/07/98	Tomich			
EX		5,801,105	09/01/98	Yano et al.			
EY		5,828,080	10/27/98	Yano et al.			
EZ		5,858,814	01/12/99	Goossen et al.			
FA		5,861,966	01/19/99	Ortel			
FB		5,883,996	03/16/99	Knapp et al.			
FC		5,995,359	11/30/99	Klee et al.			
FD		6,058,131	05/02/00	Pan			
FE		6,137,603	10/24/00	Henmi			
FF		6,146,906	11/14/00	Inoue et al.			
FG		6,173,474	01/16/01	Conrad			
FH		6,180,252	01/30/01	Farrell et al.			
FI		4,242,595	12/30/0	Lehovec			
FJ		4,398,342	08/16/83	Pitt et al.			
FK		4,424,589	01/03/84	Thomas et al.			
FL		4,876,208	10/24/89	Gustafson et al.			
FM		4,482,422	11/84	McGinn et al.			
FN		4,667,088	05/19/87	Kramer			
FO		4,772,929	09/20/88	Manchester et al.			
FP		4,841,775	06/27/89	Ikeda et al.			

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	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Fred RICHARD, t al.			
				FILING DATE November 6, 2001		GROUP 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
O T P E NOV 07 2003 PATA TRADEMARK OFFICE	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
IU	5,844,260	12/01/98	Ohori				
IV	5,846,846	12/08/98	Suh et al.				
IW	5,863,326	01/26/99	Nause et al.				
IX	5,872,493	02/16/99	Ella				
IY	5,879,956	03/99	Seon et al.				
IZ	5,880,452	03/09/99	Plesko				
JA	5,883,564	03/16/99	Partin				
JB	5,907,792	05/25/99	Droopad et al.				
JC	5,937,274	08/10/99	Kondow et al.				
JD	5,948,161	09/07/99	Kizuki				
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
KA	6,153,454	11/28/00	Krivokapic				
KB	6,191,011	02/01	Gilboa et al.				
KC	6,204,737	03/20/01	Ella				
KD	6,224,669	05/01/01	Yi et al.				
KE	6,225,051	05/01/01	Sugiyama et al.				
KF	6,241,821	06/05/01	Yu et al.				
KG	6,265,749	07/24/01	Gardner et al.				
KH	6,313,486	11/01	Kencke et al.				
KI	6,316,832	11/13/01	Tsuzuki et al.				
KJ	2002/0008234	01/02	Emrick				
KK	3,670,213	06/13/72	Nakawaga et al.				
KL	4,756,007	07/05/88	Qureshi et al.				
KM	4,773,063	09/20/88	Hunsperger et al.				
KN	5,394,489	02/28/95	Koch				
KO	5,406,202	04/11/95	Mehrgardt et al.				
KP	5,528,067	06/18/96	Farb et al.				
KQ	5,572,052	11/05/96	Kashihara et al.				
KR	5,767,543	06/16/98	Ooms et al.				
KS	6,175,497	01/16/01	Tseng et al.				
KT	6,197,503	03/06/01	Vo-Dinh et al.				
KU	6,248,459	06/19/01	Wang et al.				
KV	6,252,261	06/26/01	Usui et al.				
KW	6,255,198	07/03/01	Linthicum et al.				
KX	6,268,269	07/31/01	Lee et al.				
KY	6,291,319	09/18/01	Yu et al.				
KZ	6,316,785	11/13/01	Nunoue et al.				
LA	6,343,171	01/29/02	Yoshimura et al.				
LB	4,965,649	10/23/90	Zanio et al.				
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Allman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				

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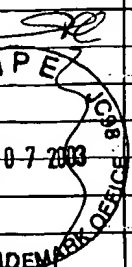
FILING DATE

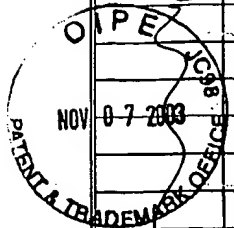
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	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
NC	5,962,069	10/05/99	Schindler et al.				
ND	5,541,422	07/30/96	Wolf et al.				
NE	5,873,977	02/23/99	Desu et al.				
NF	5,538,941	07/23/96	Findikoglu et al.				
NG	6,046,464	04/04/00	Schetzina				
NH	6,235,145	05/22/01	Li et al.				
NI	5,610,744	03/11/97	Ho et al.				
NJ	5,280,013	01/18/94	Newman et al.				
NK	6,348,373 B1	02/19/02	Ma et al.				
NL	8,339,664 B1	01/15/02	Farjady et al.				
NM	4,439,014	03/27/84	Stacy et al.				
NN	4,889,402	12/26/89	Reinhart				
NO	5,963,291	10/05/99	Wu et al.				
NP	6,011,641	01/04/00	Shin et al.				
NQ	6,340,788 B1	01/22/02	King et al.				



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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
O P F S NOV 07 2003 U.S. PATENT AND TRADEMARK OFFICE - BOSTON	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
PE	6,210,988 B1	04/03/01	Howe et al.				
PF	6,392,257	05/21/02	Ramdani et al.				
PG	4,442,590	04/17/84	Stockton et al.				
PH	5,603,764	02/18/97	Matsuda et al.				
PI	6,087,681	06/11/00	Shakuda				
PJ	5,132,648	07/21/92	Trinh et al.				
PK	6,427,066	07/30/02	Grube				
PL	2002/0072245	06/13/02	Ooms et al.				
PM	6,278,138 B1	08/21/01	Suzuki				
PN	5,888,296	03/30/99	Ooms et al.				
PO	5,198,269	03/30/93	Swartz et al.				



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QA		5,776,359	07/07/98	Schultz et al.			
QB		5,599,953	10/29/96	Kikkawa et al.			
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QF		6,277,436 B1	08/21/01	Stauf et al.			
QG		6,039,803	03/21/00	Fitzgerald et al.			
QH		5,619,051	04/08/97	Endo			
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QK		5,103,494	04/07/92	Mozer			
QL		4,594,000	06/10/86	Falk et al.			
QM		4,297,656	10/27/81	Pan			
QN		5,244,818	09/14/93	Jokers et al.			
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QP		5,484,664	01/16/96	Kitahara et al.			
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QR		6,438,281 B1	08/20/02	Tsukamoto et al.			
QS		5,399,898	03/21/95	Rostoker			
QT		6,271,619	08/07/01	Yamada et al.			
QU		5,334,556	08/02/94	Guldi			
QV		4,910,164	03/20/90	Shichijo			
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QZ		6,143,366	11/07/00	Lu			
RA		6,410,941	06/25/02	Taylor et al.			
RB		5,397,428	03/14/95	Stoner et al.			
RC		6,432,546 B1	08/13/02	Ramesh et al.			
RD		6,345,424	02/12/02	Hasegawa et al.			
RE		6,338,756 B2	01/15/02	Dietze			
RF		5,516,725	05/14/96	Chang et al.			
RG		4,667,212	05/19/87	Nakamura			
RH		5,629,534	05/13/97	Inuzuka et al.			
RI		3,914,137	10/21/75	Huffman et al.			
RJ		5,753,928	05/19/98	Krause			
RK		5,977,567	11/02/99	Verdiell			
RL		5,130,762	07/14/92	Kulick			
RM		5,621,227	04/15/97	Joshi			
RN		6,389,209 B1	05/14/02	Suhir			
RO		5,163,118	11/10/92	Lorenzo et al.			
RP		5,926,493	07/20/99	O'Brien et al.			

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	SB	5,395,663	03/07/95	Tabata et al.			
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	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
	SN	6,462,360 B1	10/08/02	Higgins, Jr. et al.			
	SO	5,981,976	11/09/99	Murasato			
	SP	5,981,980	11/09/99	Miyajima et al.			
	SQ	2002/0006245 A1	01/17/02	Kubota et al.			
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	SS	6,256,426 B1	07/03/01	Duchet			
	ST	6,278,523 B1	08/21/01	Gorecki			
	SU	6,319,730 B1	11/20/01	Ramdani et al.			
	SV	6,404,027	06/11/02	Hong et al.			
	SW	6,312,819 B1	11/06/01	Jia et al.			
	SX	5,119,448	06/02/92	Schaefer et al.			
	SY	4,120,588	10/17/78	Chaum			
	SZ	5,194,917	03/16/93	Regener			
	TA	5,018,816	05/28/91	Murray et al.			
	TB	5,953,468	09/14/99	Finnila et al.			
	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wisseman et al.			
	TE	4,934,777	06/19/90	Jou et al.			
	TF	6,320,238 B1	11/20/01	Kizilyalli et al.			
	TG	6,393,167 B1	05/21/02	Davis et al.			
	TH	5,760,427	06/02/98	Onda			
	TI	6,411,756 B2	06/25/02	Sadot et al.			
	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
	TN	5,055,835	10/08/91	Sutton			
	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
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UB	5,427,988	06/27/95	Sengupta et al.				
UC	6,297,842 B1	10/02/01	Koizumi et al.				
UD	5,682,046	10/28/97	Takahashi et al.				
UE	5,181,085	01/19/93	Moon et al.				
UF	6,051,858	04/18/00	Uchida et al.				
UG	6,013,553	01/11/00	Wallace et al.				
UH	4,872,046	10/03/89	Morkoc et al.				
UI	2002/0047123 A1	04/25/02	Ramdani et al.				
UJ	5,995,528	11/30/99	Fukunaga et al.				
UK	5,075,743	12/24/91	Behfar-Rad				
UL	5,438,584	08/01/95	Paoli et al.				
UM	4,503,540	03/05/85	Nakashima et al.				
UN	5,373,166	12/13/94	Buchan et al.				
UO	6,278,137 B1	08/21/01	Shimoyama et al.				
UP	5,623,439	04/22/97	Gotoh et al.				
UQ	4,981,714	01/01/91	Ohno et al.				
UR	6,194,753 B1	02/27/01	Seon et al.				
US	6,326,637 B1	12/04/01	Parkin et al.				
UT							
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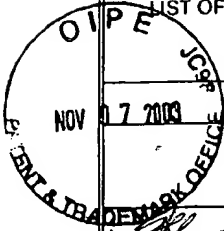
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AAH	0 999 600	05/10/00	EP	X	
AAI	1 319 311	06/04/70	Great Britain	X	
AAJ	5-291299	11/05/93	Japan w/English Abstract	X	
AAK	11-238683	08/31/99	Japan	X	
AAL	11-260835	09/24/99	Japan w/English Abstract	X	
AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
AAN	5-48072	02/26/93	Japan w/English Abstract	X	
AAO	52-88354	07/23/77	Japan w/English Abstract	X	
AAP	54-134554	10/19/79	Japan w/English Abstract	X	
AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
AAR	61-108187	05/26/86	Japan w/English Abstract	X	
AAS	6-232126	08/19/94	Japan	X	
AAT	6-291299	10/18/94	Japan w/English Abstract	X	
AAU	63-34994	02/15/88	Japan w/English Abstract	X	
AAV	63-131104	06/03/88	Japan w/English Abstract	X	
AAW	63-198365	08/17/88	Japan w/English Abstract	X	
AAX	10-321943	12/04/98	Japan	X	
AAZ	6-334168	12/02/94	Japan	X	
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ABB	WO 99/14804	03/25/99	WIPO	X	
ABB	WO 97/45827	12/04/97	WIPO		
ABC	WO 99/19546	04/22/99	WIPO		
ABD	WO 00/33363	06/08/00	WIPO		
ABE	WO 00/48239	08/17/00	WIPO		
ABF	WO 99/14797	03/25/99	WIPO		
ABG	GB 2 335 792	09/29/99	Great Britain		
ABH	1 109 212	06/20/01	Europe		
ABI	DE 197 12 496	10/30/97	Germany		X
ABJ	60-212018	10/24/85	Japan w/English Abstract		
ABK	60-210018	10/22/85	Japan w/English Abstract		
ABL	WO 92/10875	06/25/92	WIPO		
ABM	0 682 266	11/15/95	Europe		
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BAA	1 043 426	10/11/00	Europe		
BAB	2000-068466	03/00	Japan (Abstract)		
BAC	64-50575	02/27/89	Japan		
BAD	WO 98/05807	01/12/98	WIPO		
BAE	WO 94/03908	02/17/94	WIPO		
BAF	WO 01/33585	05/10/01	WIPO		
BAG	1-102435	04/20/89	Japan w/English Abstract		
BAH	52-135684	11/12/77	Japan (English Abstract)		
BAI	02051220	02/21/90	Japan (English Abstract)		
BAJ	11135614	05/21/99	Japan (w/English Abstract)		
BAK	64-52329	02/28/89	Japan (w/English Abstract)		
BAL	10-256154	09/25/98	Japan (w/English Abstract)		
BAM	DE 196 07 107	08/28/97	Germany		xx
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BAO	58-213412	12/12/83	Japan w/English Abstract		
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BAR	61-63015	04/01/86	Japan w/English Abstract		
BAS	11340542	12/10/99	Japan (English Abstract)		
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BAU	0 331 467	09/06/89	Europe		
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BAW	0 926 739	06/30/99	Europe		
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BAY	5-152529	06/18/93	Japan w/English Abstract		
BAZ	9-67193	03/11/97	Japan w/English Abstract		
BBA	9-82913	03/28/97	Japan w/English Abstract		
BBB	0 309 270	03/29/89	Europe		
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BBD	EP 0 810 666	12/03/97	Europe		
BBE	1-179411	07/17/89	Japan w/English Abstract		
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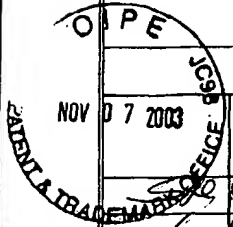
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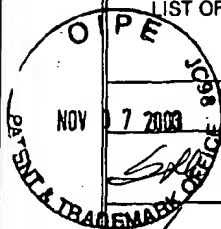
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CAF	61-36981	02/21/86	Japan w/English Abstract			
CAG	WO 93/07647	04/15/93	WIPO			
CAH	2002-9366	01/11/02	Japan w/English Abstract			
CAI	EP 0 881 669	12/02/98	Europe			
CAJ	WO 02/03480	01/10/02	WIPO			
CAK	WO 02/50879	06/27/02	WIPO			
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CAM	WO 01/04943 A1	01/18/01	WIPO			xx
CAN	WO 02/47127 A2	06/13/02	WIPO			
CAO	JP 58-075868	05/07/83	Japan w/English Abstract			
CAP	EP 0 993 027	04/12/00	Europe			
CAQ	EP 0 711 853	05/15/96	Europe			
CAR	WO 98/20606	05/14/98	WIPO			
CAS	EP 1 043 765	10/11/00	Europe			
CAT	0 300 499	01/25/89	Europe			
CAU	EP 1 085 319	03/21/01	Europe			
CAV	WO 01/16395	03/08/01	WIPO			
CAW	2000-351692	12/19/00	Japan w/English Abstract			
CAX	03-188619	08/16/91	Japan (English Abstract only)			
CAY	63-289812	11/28/88	Japan (English Abstract only)			
CAZ	EP 0 884 767	12/16/98	Europe			
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CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO <sub>3</sub> Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.		
CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.		
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", 1998 <i>Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.		
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col. and Motorola Labs, May 11, 2000.		
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.		
CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.		
CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," 1997 <i>Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.		
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CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.		
CCAJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.		
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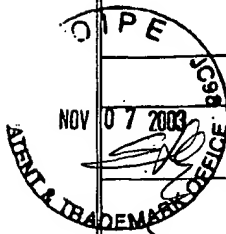
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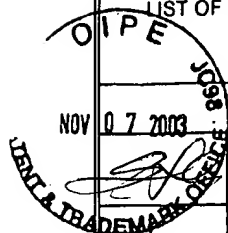
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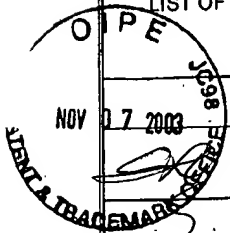
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JJAB	P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114		
JJAC	Wang et al.; "Depletion-Mode GaAs MOSFETs with Negligible Drain Current Drift and Hysteresis"; Electron Devices Meeting, 1998, IEDM '98 Technical Digest; pp. 67-70		
JJAD	Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322		
JJAE	A.Y. Wu et al.; "Highly Oriented (Pb,Lu)(Zr,Ti)O <sub>3</sub> Thin Films on Amorphous Substrates"; IEEE, 1992; pp. 301-304		
JJAF	Timothy E. Glassman et al.; "Evidence for Cooperative Oxidation of MoCVD Precursors Used in Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> Film Growth"; Mat. Res. Soc. Symp. Proc. Vol. 446, 1997 Materials Research Society; pp. 321-326		
JJAG	S.N. Subbarao et al.; "Monolithic PIN Photodetector and FET Amplifier on GaAs-os-Si"; IEEE; GaAs IC Symposium-163-166; 1989		
JJAH	T.A. Langdo et al.; "High Quality Ge on Si by Epitaxial Necking"; Applied Physics Letters; Vol. 76, No. 25; pp. 3700-3702; June 19, 2000		
JJAI	Chenning Hu et al.; Solar Cells From Basics to Advanced Systems; McGraw-Hill Book Company; 1983		
JJAJ	O.J. Painter et al.; "Room Temperature Photonic Crystal Defect Lasers at Near-Infrared Wavelengths in InGaAsP"; Journal of Lightwave Technology, Vol. 17, No. 11; November 1999		
JJAK	C. Donn et al.; "A 16-Element, K-Band Monolithic Active Receive Phased Array Antenna"; Antennas and Propagation Society International Symposium, 1988; pp.188-191, Vol. 1; 6-10 June 1988		
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JJAN	P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract)		
JJAO	Ranu Nayak et al.; "Enhanced acousto-optic diffraction efficiency in a symmetric SrTiO <sub>3</sub> /BaTiO <sub>3</sub> /SrTiO <sub>3</sub> thin-film heterostructure"; 1 November 2000; Vol. 39, No. 31; Applied Optics; pp. 5847-5853		
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KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002		
KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5		
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KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO <sub>3</sub> Waveguides for Fabricating Micro-Optics Using Wet-Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056		
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KKA O			
KKAP			
KKAQ			
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EX	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
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	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
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	VE	6,113,225	09/05/00	Miyata et al.			
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	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
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*Shouwang Shu*

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	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
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	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
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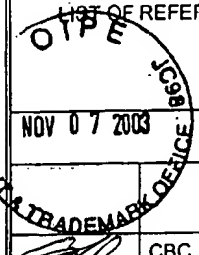
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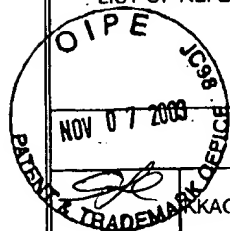
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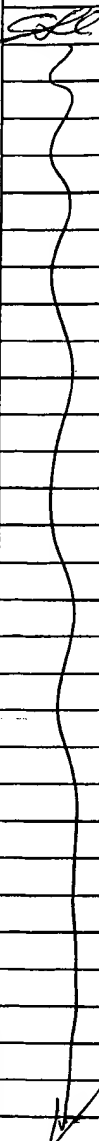
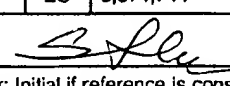
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	CBC	EP 1 035 759	09/13/00	Europe			
	CBD	EP 0 860 913	08/26/95	EUROPE			
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT			
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT			
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT			
	CBH	EP 1 089 338	04/04/01	EUROPE			
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)			
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)			
	CBK	03-149882	11/07/89	JAPAN			
	CBL	0 614 256	09/07/94	EUROPE			
	CBM	01 054 442	11/22/00	EUROPE			
	CBN	0 852 416	07/08/98	EUROPE			
	CBO	W0 02/08806	01/31/02	WIPO			
	CBP	W0 01/59837	08/16/01	WIPO			
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT			
	CBR	0 600 658	06/08/94	EUROPE			
	CBS	0 412 002	02/06/91	EUROPE			
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	CBW	0 661 561	07/05/95	EUROPE			
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	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
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	XY	4,298,247	11/03/81	MICHELET ET AL			
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	YA	3,758,199	09/11/73	THAXTER			
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	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
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	YO	5,362,998	11/08/94	IWAMURA ET AL			
	YP	5,188,976	02/23/93	KUME ET AL			
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	YR	5,919,515	07/06/99	YANO ET AL			
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	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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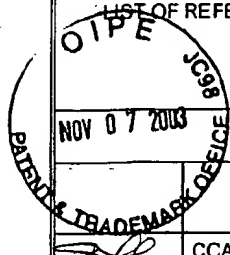
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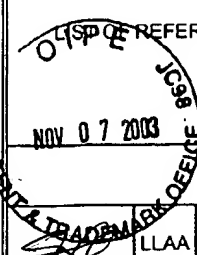
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
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